

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE (Rev. 2-32) PATENT AND TRADEMARK OFFICE Information Disclosure Statement by Applicant (Use several sheets if necessary)	ATTY. DOCKET NO. SAR 14108	SERIAL NO To Be Assigned
	APPLICANT John Robertson Tower et al.	
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U.S. PTO
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08/30/01

U.S. PATENT DOCUMENTS

Exmr Initial	Document Number	Date	Name	Class	Sub Class	Filing Date
<i>sa</i>	4,608,606	08/26/86	Levine			
<i>sa</i>	5,981,932	11/09/99	Guerrieri et al.			
<i>sa</i>	3,953,733	04/27/76	Levine			
<i>sa</i>	5,151,380	09/29/92	Hynecek			
<i>sa</i>	5,453,632	09/26/95	Hynecek et al.			
<i>sa</i>	4,668,971	05/26/87	Hynecek			
<i>sa</i>	4,229,752	10/21/80	Hynecek			
<i>sa</i>	5,841,159	11/24/98	Lee et al.			
<i>sa</i>	5,881,184	03/09/99	Guidash			
<i>sa</i>	6,069,376	05/30/00	Merrill			
<i>sa</i>	6,141,050	10/31/00	Ackland et al.			
<i>sa</i>	5,591,996	01/07/97	Haigh et al.			
<i>sa</i>	5,742,047	04/21/98	Buhler et al.			
<i>sa</i>	5,808,329	09/15/98	Jack et al.			

FOREIGN PATENT DOCUMENTS

Exmr Initial	Document Number	Date	Country	Class	Sub Class	Translation YES NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

<i>sa</i>	1)	W. F. Keenan et al.; "A Channel-Stop-Defined Barrier and Drain Antiblooming Structure for Virtual Phase CCD Image Sensors"; IEEE Transactions on Electron Devices, vol. 36, no. 9; September 1989.
<i>sa</i>	2)	Y. Matsunaga et al.; "A Highly Sensitive On-Chip Charge Detector for CCD Area Image Sensor"; IEEE Journal of Solid-State Circuits, vol. 26, no. 4, April 1991.
<i>sa</i>	3)	S. Ohsawa et al.; "Analysis of Low Signal Level Characteristics for High-Sensitivity CCD Charge Detector"; IEEE Transactions on Electron Devices, vol. 39, no. 6, June 1992.
<i>sa</i>	4)	Y. Matsunaga et al.; "Ultra High Sensitivity On-Chip Amplifier for VLSI CCD Image Sensor"; ULSI Research Center; 1990 Symposium on VLSI Circuits
<i>sa</i>	5)	E. Roks et al.; "The Double-Sided Floating-Surface Detector: An Enhanced Charge-Detection Architecture For CCD Image Sensors"; IEEE Transactions on Electron Devices, vol. 43, no. 9, September 1996.
<i>sa</i>	6)	B. C. Burkey et al.; "The Pinned Photodiode for an Interline-Transfer CCD Image Sensor"; Research Laboratories, Eastman Kodak Company; December 1984; pgs. 28-31.
<i>sa</i>	7)	E. Meisenzahl et al.; "Charge-Coupled Device Image Sensors"; January 1998; http://www.sensormag.com/articles/0198/cc0198/main.shtml
<i>sa</i>	8)	"An Introduction to Scientific Imaging Charge-Coupled Devices, SiTe CCD Technology for Superior Performance"; Scientific Imaging Technologies, Inc.; 1994.

Examiner <i>Samuel Adams</i>	Date Considered <i>12/27/02</i>
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Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.